

NP60N055VUK

R07DS0588EJ0100

Rev.1.00

Dec 12, 2011

MOS FIELD EFFECT TRANSISTOR

Description

The NP60N055VUK is N-channel MOS Field Effect Transistor designed for high current switching applications.

Features

- Super low on-state resistance
 $R_{DS(on)} = 5.5 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 30 \text{ A)}$
- Low C_{iss} : $C_{iss} = 2500 \text{ pF TYP. (} V_{DS} = 25 \text{ V)}$
- Designed for automotive application and AEC-Q101 qualified

Ordering Information

Part No.	Lead Plating	Packing		Package
NP60N055VUK-E1-AY ^{*1}	Pure Sn (Tin)	Tape 2500 p/reel	Taping (E1 type)	TO-252 (MP-3ZP)
NP60N055VUK-E2-AY ^{*1}			Taping (E2 type)	

Note: ^{*1} Pb-free (This product does not contain Pb in the external electrode)

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to Source Voltage ($V_{GS} = 0 \text{ V}$)	V_{DSS}	55	V
Gate to Source Voltage ($V_{DS} = 0 \text{ V}$)	V_{GSS}	± 20	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$)	$I_{D(DC)}$	± 60	A
Drain Current (pulse) ^{*1}	$I_{D(pulse)}$	± 240	A
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_{T1}	105	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_{T2}	1.2	W
Channel Temperature	T_{ch}	175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 175	$^\circ\text{C}$
Repetitive Avalanche Current ^{*2}	I_{AR}	25	A
Repetitive Avalanche Energy ^{*2}	E_{AR}	63	mJ

Notes: ^{*1} $T_C = 25^\circ\text{C}$, $P_W \leq 10 \text{ }\mu\text{s}$, Duty Cycle $\leq 1\%$

^{*2} $R_G = 25 \text{ }\Omega$, $V_{GS} = 20 \rightarrow 0 \text{ V}$

Thermal Resistance

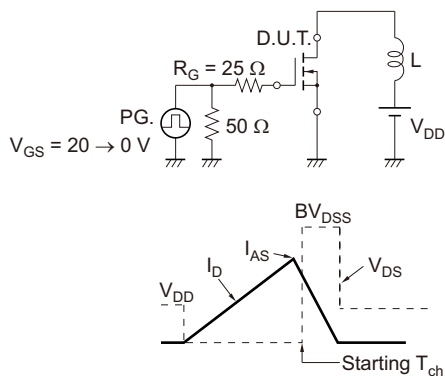
Channel to Case Thermal Resistance	$R_{th(ch-C)}$	1.43	$^\circ\text{C/W}$
Channel to Ambient Thermal Resistance	$R_{th(ch-A)}$	125	$^\circ\text{C/W}$

Electrical Characteristics ($T_A = 25^\circ\text{C}$)

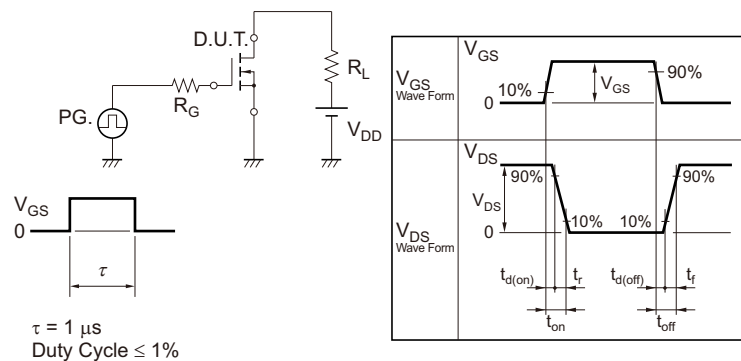
Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 55\text{ V}, V_{GS} = 0\text{ V}$
Gate Leakage Current	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$
Gate to Source Threshold Voltage	$V_{GS(th)}$	2.0	3.0	4.0	V	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$
Forward Transfer Admittance ^{*1}	$ y_{fs} $	22	44	—	S	$V_{DS} = 5\text{ V}, I_D = 30\text{ A}$
Drain to Source On-state Resistance ^{*1}	$R_{DS(on)}$	—	4.6	5.5	m Ω	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$
Input Capacitance	C_{iss}	—	2500	3750	pF	$V_{DS} = 25\text{ V}$ $V_{GS} = 0\text{ V}$ $f = 1\text{ MHz}$
Output Capacitance	C_{oss}	—	260	390	pF	
Reverse Transfer Capacitance	C_{rss}	—	100	180	pF	
Turn-on Delay Time	$t_{d(on)}$	—	19	50	ns	$V_{DD} = 28\text{ V}, I_D = 30\text{ A}$ $V_{GS} = 10\text{ V}$ $R_G = 0\text{ }\Omega$
Rise Time	t_r	—	7	20	ns	
Turn-off Delay Time	$t_{d(off)}$	—	45	90	ns	
Fall Time	t_f	—	5	20	ns	
Total Gate Charge	Q_G	—	42	63	nC	$V_{DD} = 44\text{ V}$ $V_{GS} = 10\text{ V}$ $I_D = 60\text{ A}$
Gate to Source Charge	Q_{GS}	—	11	—	nC	
Gate to Drain Charge	Q_{GD}	—	10	—	nC	
Body Diode Forward Voltage ^{*1}	$V_{F(S-D)}$	—	0.9	1.5	V	$I_F = 60\text{ A}, V_{GS} = 0\text{ V}$
Reverse Recovery Time	t_{rr}	—	44	—	ns	$I_F = 60\text{ A}, V_{GS} = 0\text{ V}$
Reverse Recovery Charge	Q_{rr}	—	45	—	nC	$di/dt = 100\text{ A}/\mu\text{s}$

Note: ^{*1} Pulsed test

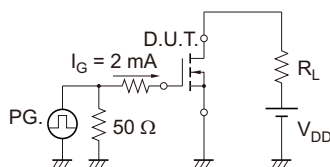
TEST CIRCUIT 1 AVALANCHE CAPABILITY



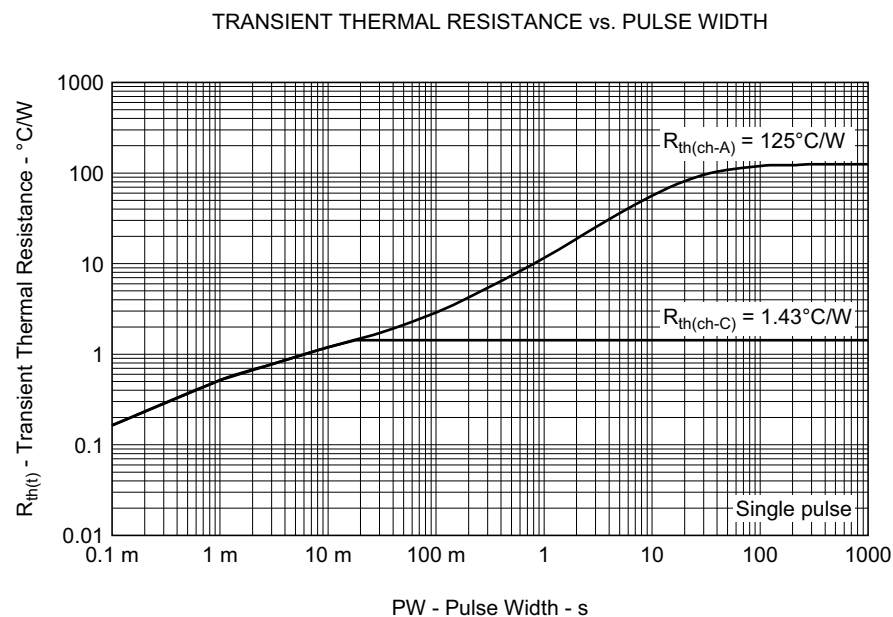
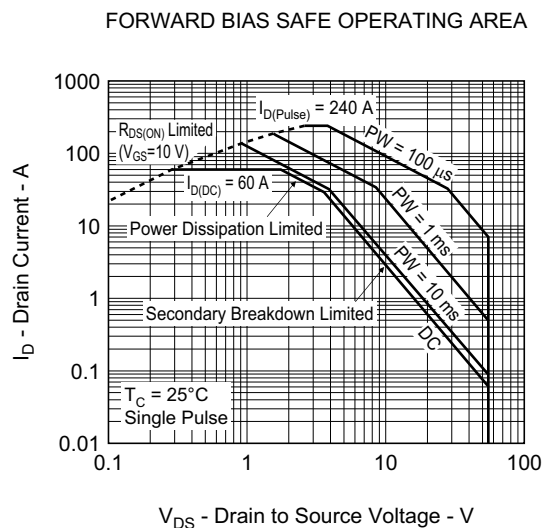
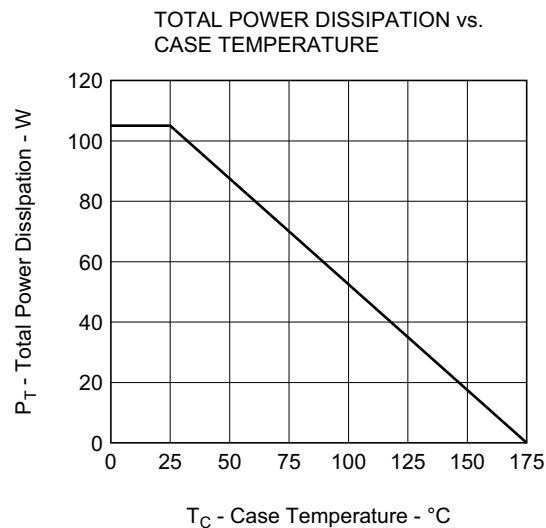
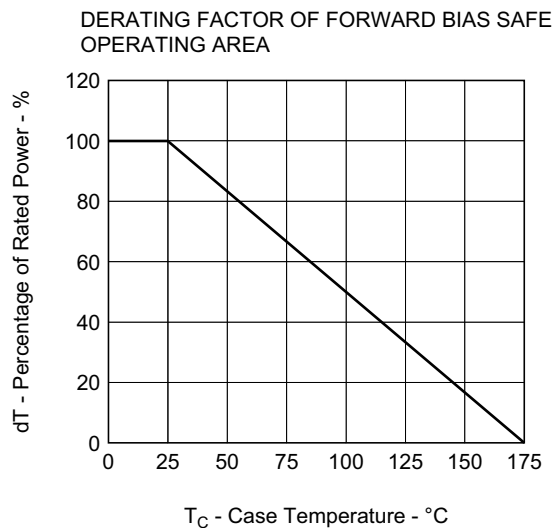
TEST CIRCUIT 2 SWITCHING TIME

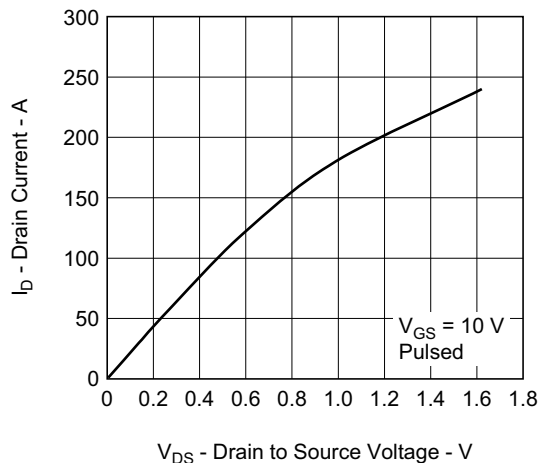


TEST CIRCUIT 3 GATE CHARGE

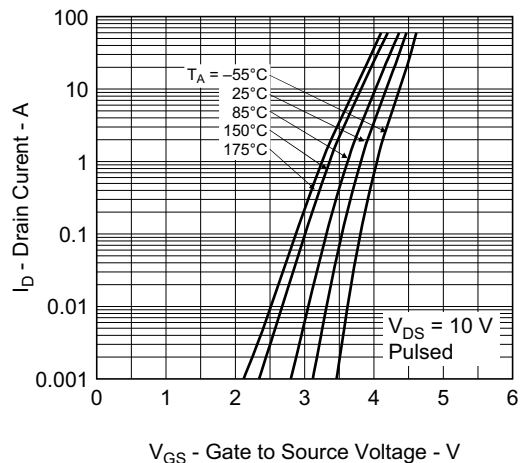
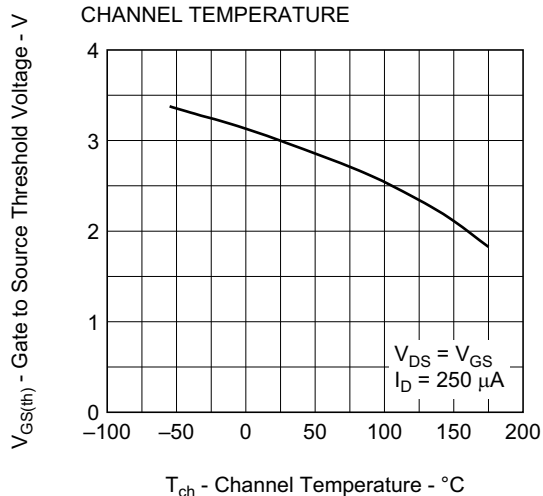
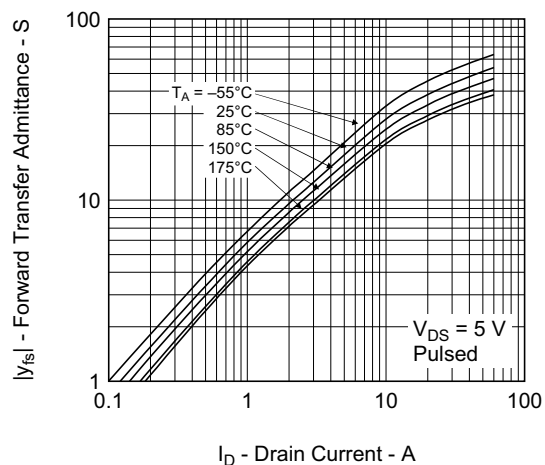
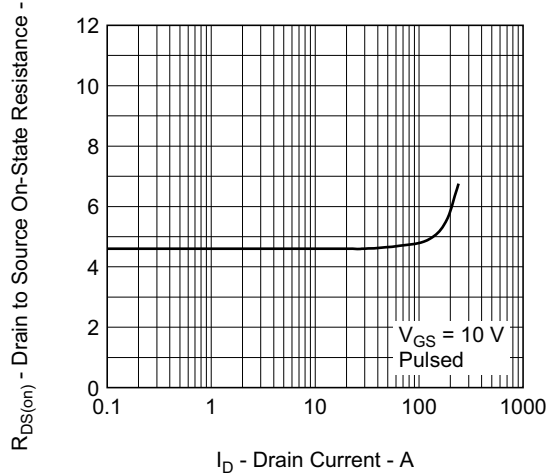
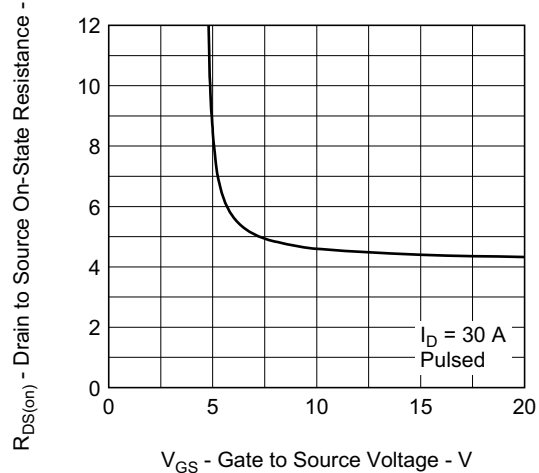


Typical Characteristics ($T_A = 25^\circ\text{C}$)

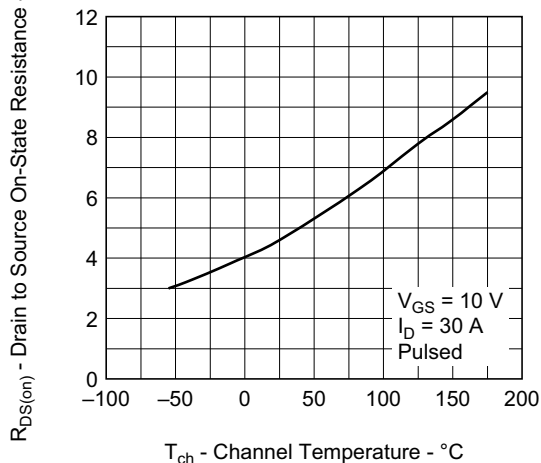


DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE

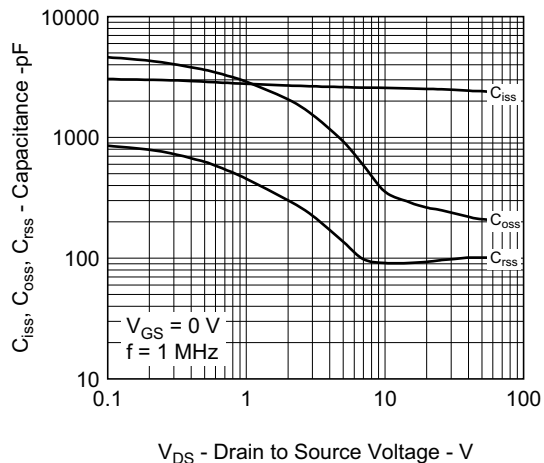
FORWARD TRANSFER CHARACTERISTICS

GATE TO SOURCE THRESHOLD VOLTAGE vs.
CHANNEL TEMPERATUREFORWARD TRANSFER ADMITTANCE vs.
DRAIN CURRENTDRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENTDRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE

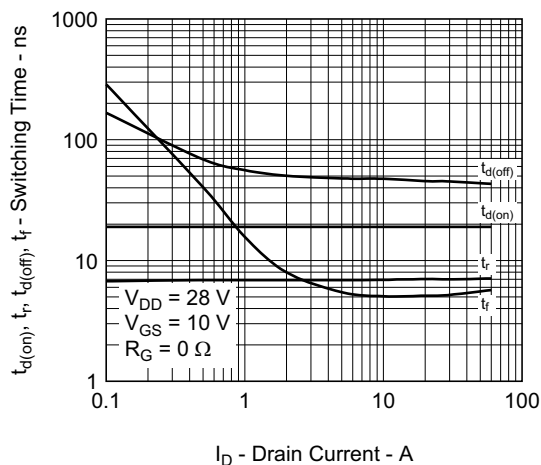
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



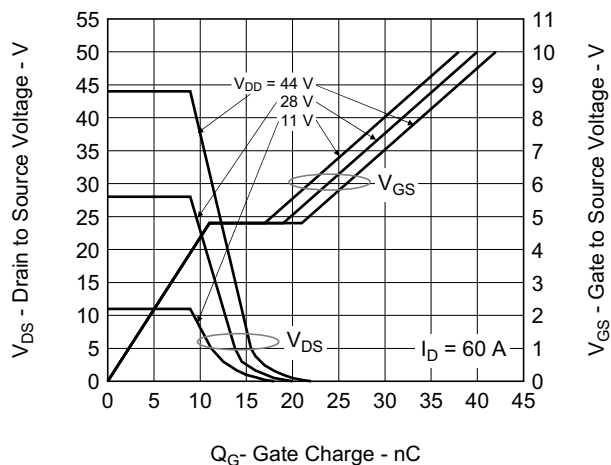
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



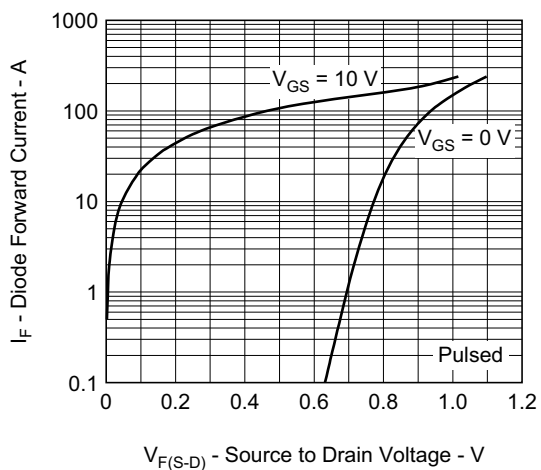
SWITCHING CHARACTERISTICS



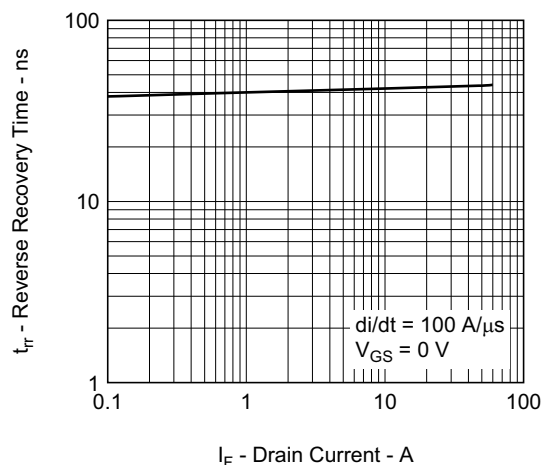
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



REVERSE RECOVERY TIME vs. DRAIN CURRENT



Revision History	NP60N055VUK Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	Dec 12, 2011	—	First Edition Issued

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